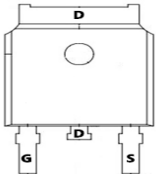
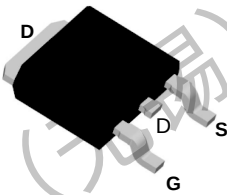
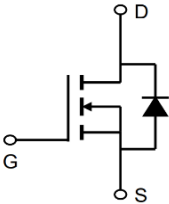




TM30N02D

N-Channel Enhancement Mosfet

General Description • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant Applications • Load switch • PWM	General Features $V_{DS} = 20V$ $I_D = 30A$ $R_{DS(ON)} = 8.8m\Omega(\text{typ.}) @ V_{GS} = 4.5V$ 100% UIS Tested 100% R_g Tested			
D:TO-252-3L				
				
Marking: 30N02				
Absolute Maximum Ratings ($T_c = 25^{\circ}C$ Unless Otherwise Noted)				
Symbol	Parameter		Rating	Units
V_{DS}	Drain-Source Voltage		20	V
V_{GS}	Gate-Source Voltage		± 20	V
$I_D@T_c=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$		30	A
$I_D@T_c=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$		19	A
I_{DM}	Pulsed Drain Current ²		111	A
EAS	Single Pulse Avalanche Energy ³		12.1	mJ
I_{AS}	Avalanche Current		11	A
$P_D@T_c=25^{\circ}C$	Total Power Dissipation ³		5	W
T_{STG}	Storage Temperature Range		-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range		-55 to 150	$^{\circ}C$
Thermal Data				
Symbol	Parameter		Typ.	Max.
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	62	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	6.6	$^{\circ}C/W$



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N-Channel Enhancement Mosfet

Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0 V, I _D = 250μA	20	-	-	V
Gate Leakage Current	I _{GSS}	V _{GS} = ±12V, V _{DS} = 0 V	-	-	±100	nA
Drain Cut-off Current	I _{DSS}	V _{DS} = 20V, V _{GS} = 0 V	-	-	1	μA
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D = 250μA	0.45	0.7	1	V
Drain-Source On-State Resistance ³	R _{DS(on)}	V _{GS} = 4.5V, I _D =5A	-	8.8	13	mΩ
		V _{GS} = 2.5V, I _D = 4.7A	-	12	20	
Dynamic Characteristics ⁴						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 10V, f = 1MHz	-	700	-	pF
Output Capacitance	C _{oss}		-	120	-	
Reverse Transfer Capacitance	C _{rss}		-	105	-	
Switching Characteristics ⁴						
Total Gate Charge	Q _g	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 5A	-	10.5	-	nC
Gate-Source Charge	Q _{gs}		-	2	-	
Gate-Drain Charge	Q _{gd}		-	2.5	-	
Turn-On Time	t _{d(on)}	V _{GEN} = 5V, V _{DD} = 10V, I _D = 5A,R _G = 3Ω,	-	10	-	ns
Rise Time	t _r		-	20	-	
Turn-Off Time	t _{d(off)}		-	32	-	
Fall Time	t _f		-	12	-	
Source-Drain Diode Characteristics						
Body Diode Voltage ³	V _{SD}	I _S =4A, V _{GS} = 0V	-	-	1.2	V
Continuous Source Current	I _S		-	-	30	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)} = 150°C.
2. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width ≤ 300μs, duty cycle ≤ 2%.
4. This value is guaranteed by design hence it is not included in the production test.



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Typical Characteristics

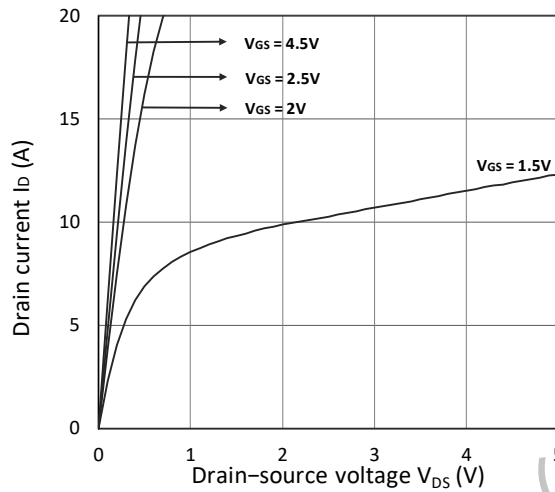


Figure 1. Output Characteristics

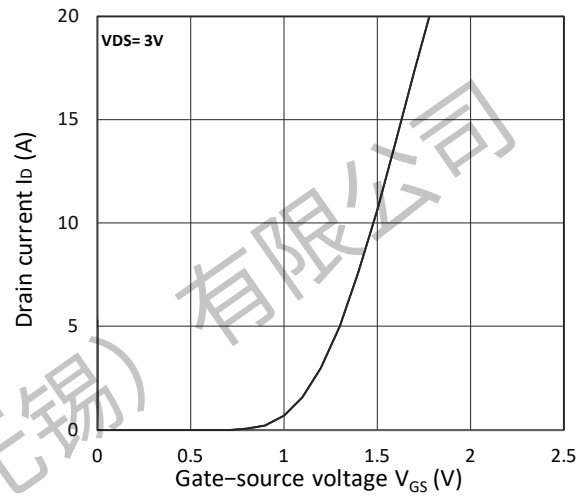


Figure 2. Transfer Characteristics

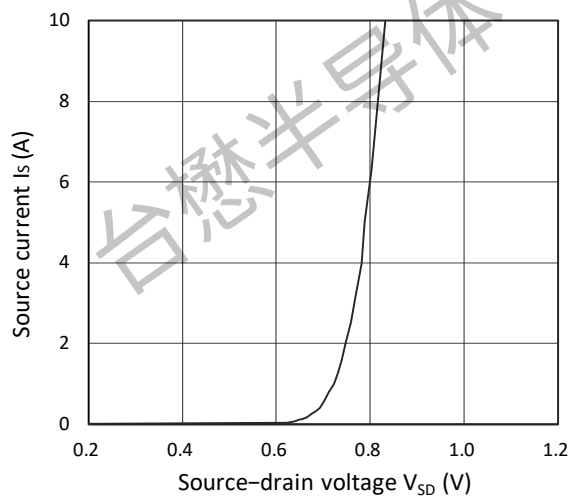


Figure 3. Forward Characteristics of Reverse

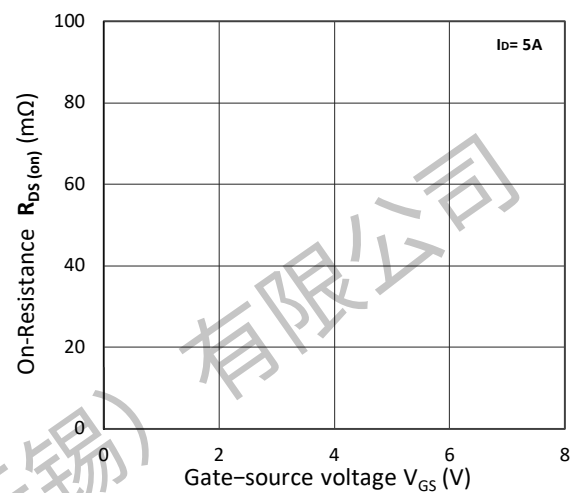


Figure 4. $R_{DS(on)}$ vs. V_{GS}

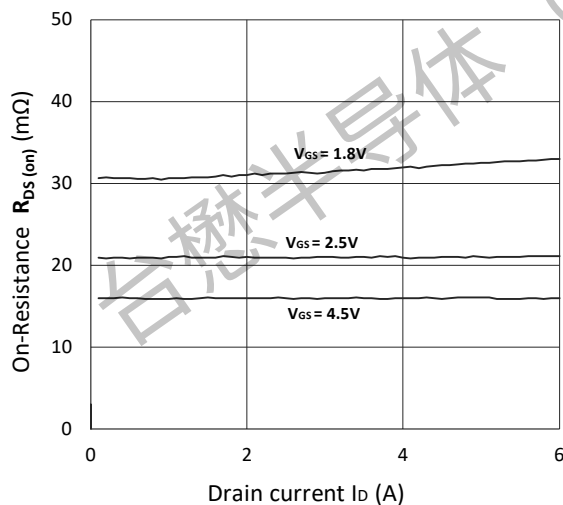


Figure 5. $R_{DS(on)}$ vs. I_D

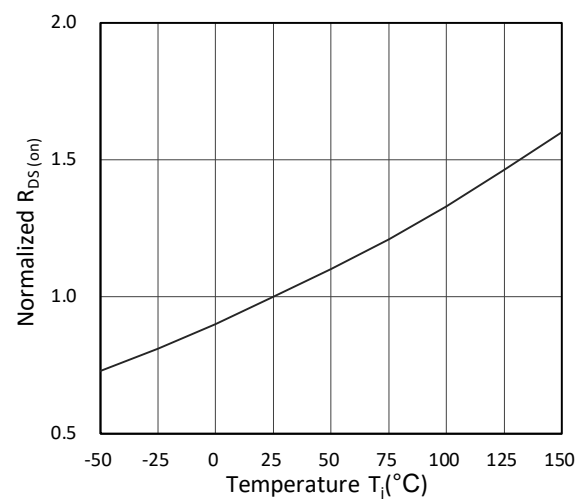


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature



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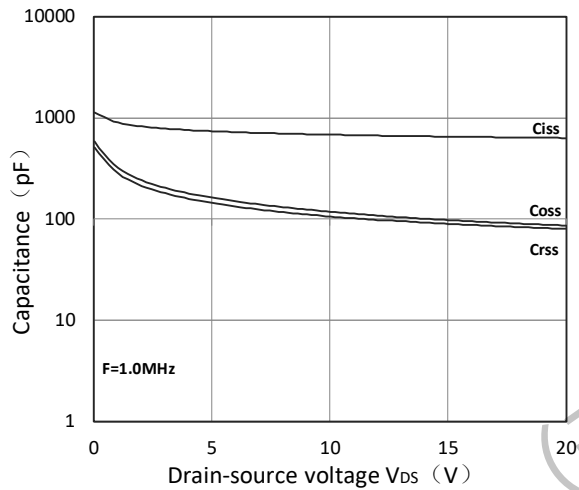


Figure 7. Capacitance Characteristics

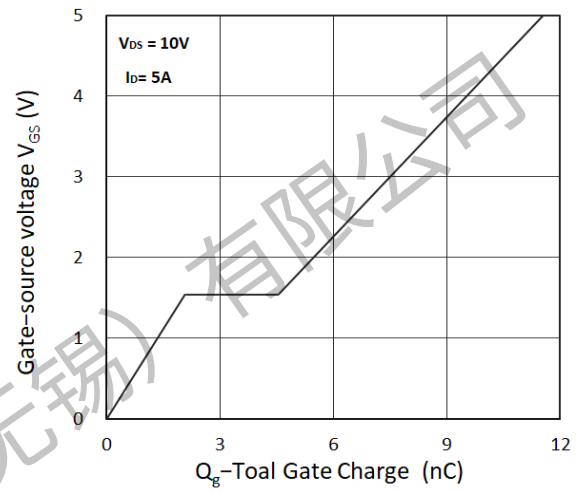


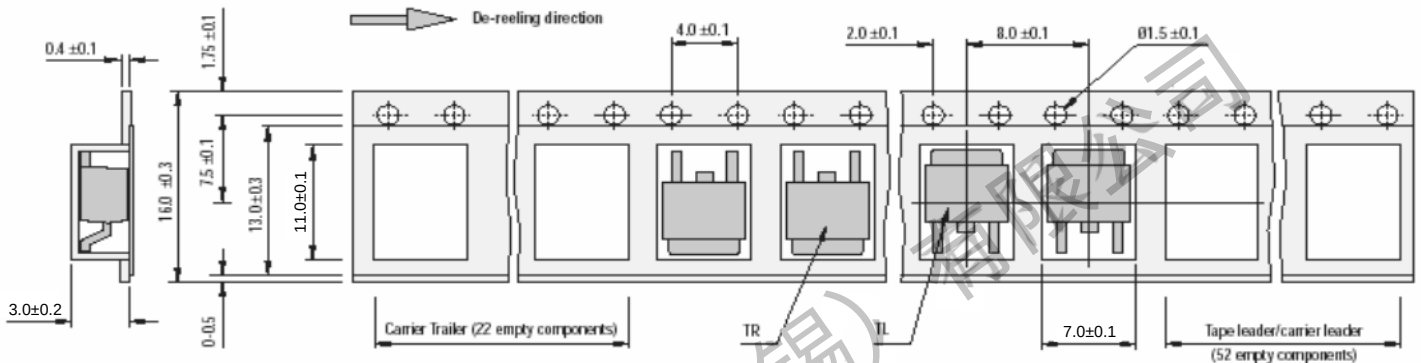
Figure 8. Gate Charge Characteristics



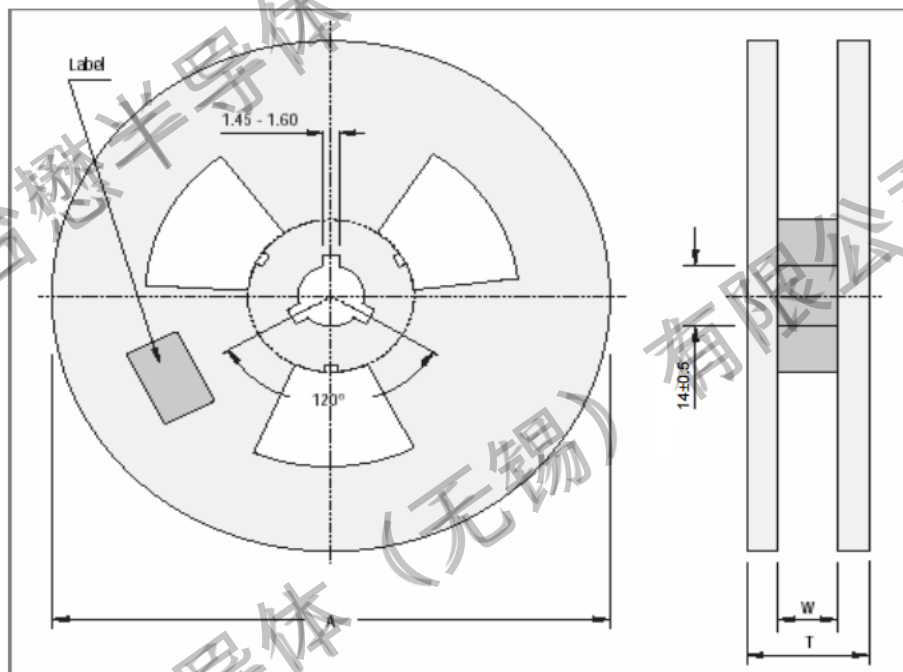
TM30N02D

N-Channel Enhancement Mosfet

TO-252-3L Embossed Carrier Tape



TO-252-3L Reel



All Dimensions are in mm.

Reel Specifications				
Package	Tape Width	Reel Dia. A - Max	Inside Thickness W	Reel Thickness T - max
TO-252-3L	16	330	18.0 ± 1.5	20

Packaging Information

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
2,500 pcs	13 inch	5,000 pcs	355×370×50	25,000 pcs	380×275×380	

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Revision history:

Date	Rev	Description	Page
2023.05.09	23.05	Original	